

# N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD16410Q5A

#### **FEATURES**

- Ultra Low Qg and Qgd
- Low Thermal Resistance
- Avalanche Rated
- · Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5mm x 6mm Plastic Package

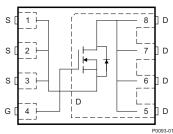
## **APPLICATIONS**

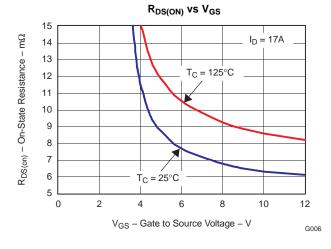
- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Control FET Applications

#### DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.







## **PRODUCT SUMMARY**

V <sub>DS</sub>	Drain to Source Voltage	25	V	
$Q_g$	Gate Charge Total (4.5V)	3.9	nC	
$Q_{gd}$	Gate Charge Gate to Drain	1.1		nC
Б	Design to Course On Basistana	V <sub>GS</sub> = 4.5V	9.6	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	V <sub>GS</sub> = 10V	6.8	mΩ
V <sub>GS(th)</sub>	Threshold Voltage	1.9		V

#### **ORDERING INFORMATION**

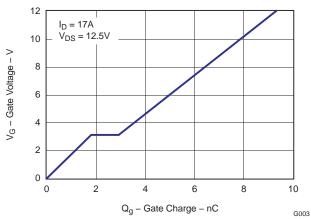
Device	Package	Media	Qty	Ship	
CSD16410Q5A	SON 5X6 Plastic Package	13-inch reel	2500	Tape and Reel	

#### **ABSOLUTE MAXIMUM RATINGS**

T <sub>A</sub> = 2	5°C unless otherwise stated	VALUE	UNIT
$V_{DS}$	Drain to Source Voltage	25	٧
$V_{GS}$	Gate to Source Voltage	+16 / -12	٧
	Continuous Drain Current, T <sub>C</sub> = 25°C	59	Α
I <sub>D</sub>	Continuous Drain Current <sup>(1)</sup>	16	Α
$I_{DM}$	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	158	Α
$P_D$	Power Dissipation <sup>(1)</sup>	3	W
$T_J$ , $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to 150	ů
E <sub>AS</sub>	Avalanche Energy, single pulse $I_D=32A,\ L=0.1mH,\ R_G=25\Omega$	51	mJ

- (1)  $R_{\theta,JA} = 42^{\circ}\text{C/W}$  on  $1\text{in}^2$  Cu (2 oz.) on 0.060" thick FR4 PCB.
- (2) Pulse width ≤300µs, duty cycle ≤2%

#### Gate Charge



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

NexFET is a trademark of Texas Instruments.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## **ELECTRICAL CHARACTERISTICS**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	haracteristics	·				
BV <sub>DSS</sub>	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25			V
I <sub>DSS</sub>	Drain to Source Leakage Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 20V			1	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = +16/-12V			100	nA
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.6	1.9	2.3	V
D	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 17A$		9.6	12	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 10V, I_D = 17A$		6.8	8.5	$m\Omega$
9 <sub>fs</sub>	Transconductance	$V_{DS} = 15V, I_D = 17A$		38		S
Dynamic	Characteristics	·	· -			
C <sub>ISS</sub>	Input Capacitance		570		740	pF
Coss	Output Capacitance	$V_{GS} = 0V$ , $V_{DS} = 12.5V$ , $f = 1MHz$		460	600	pF
C <sub>RSS</sub>	Reverse Transfer Capacitance			40	52	pF
$R_g$	Series Gate Resistance			0.7	1.4	Ω
Qg	Gate Charge Total (4.5V)			3.9	5	nC
Q <sub>gd</sub>	Gate Charge Gate to Drain	V <sub>DS</sub> = 12.5V, I <sub>D</sub> = 17A		1.1		nC
Q <sub>gs</sub>	Gate Charge Gate to Source	$V_{DS} = 12.5V, I_D = 17A$		1.8		nC
Qg(th)	Gate Charge at Vth			1.1		nC
Q <sub>OSS</sub>	Output Charge	$V_{DS} = 13V, V_{GS} = 0V$		10		nC
t <sub>d(on)</sub>	Turn On Delay Time			6.2		ns
t <sub>r</sub>	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V, I_{D} = 17A$		10.7		ns
t <sub>d(off)</sub>	Turn Off Delay Time	$R_G = 2\Omega$		6.5		ns
t <sub>f</sub>	Fall Time			3.6		ns
Diode Cl	haracteristics					
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> = 17A, V <sub>GS</sub> = 0V		0.85	1	V
Q <sub>rr</sub>	Reverse Recovery Charge	$V_{DD} = 13V$ , $I_F = 17A$ , $di/dt = 300A/\mu s$		14		nC
t <sub>rr</sub>	Reverse Recovery Time	$V_{DD} = 13V$ , $I_F = 17A$ , $di/dt = 300A/\mu s$		18.2		ns

## THERMAL CHARACTERISTICS

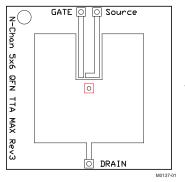
(T<sub>A</sub> = 25°C unless otherwise stated)

	PARAMETER	MIN	TYP	MAX	UNIT
R $_{\theta JC}$	Thermal Resistance Junction to Case <sup>(1)</sup>			3.8	°C/W
R $_{\theta JA}$	Thermal Resistance Junction to Ambient <sup>(1)</sup> (2)			52	°C/W

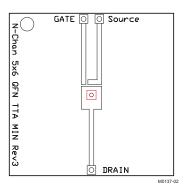
R<sub>0,JC</sub> is determined with the device mounted on a 1 inch square 2 oz. Cu pad on a 1.5 x 1.5 in 0.060 inch thick FR4 board. R<sub>0,JC</sub> is specified by design while  $R_{\theta,JA}$  is determined by the user's board design. Device mounted on FR4 Material with 1 inch<sup>2</sup> of 2 oz. Cu.

Submit Documentation Feedback





Max  $R_{\theta JA} = 52^{\circ}C/W$  when mounted on 1 inch<sup>2</sup> of 2 oz. Cu.



Max  $R_{\theta JA} = 121^{\circ}C/W$  when mounted on minimum pad area of 2 oz. Cu.

## TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

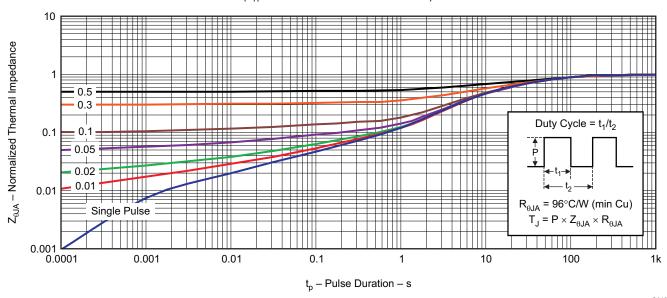


Figure 1. Transient Thermal Impedance

G012



# **TYPICAL MOSFET CHARACTERISTICS (continued)**

# (T<sub>A</sub> = 25°C unless otherwise stated)

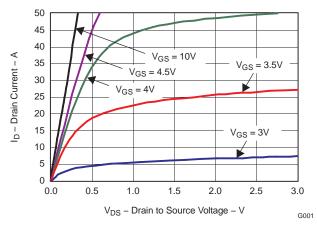


Figure 2. Saturation Characteristics

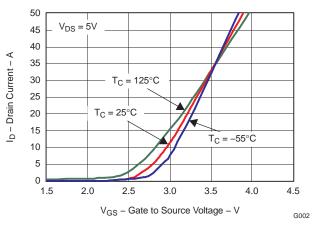


Figure 3. Transfer Characteristics

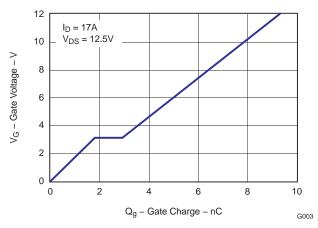


Figure 4. Gate Charge

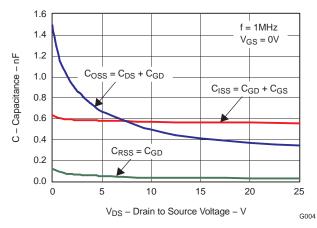


Figure 5. Capacitance

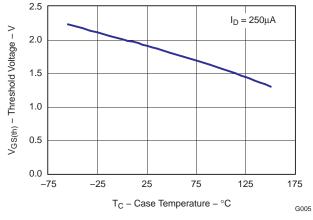


Figure 6. Threshold Voltage vs. Temperature

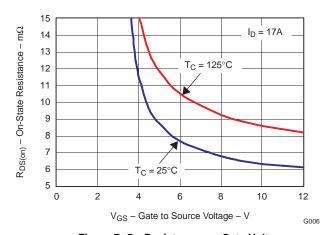


Figure 7. On Resistance vs. Gate Voltage



# **TYPICAL MOSFET CHARACTERISTICS (continued)**

# (T<sub>A</sub> = 25°C unless otherwise stated)

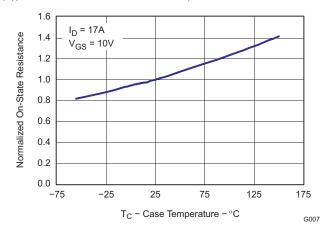


Figure 8. On Resistance vs. Temperature

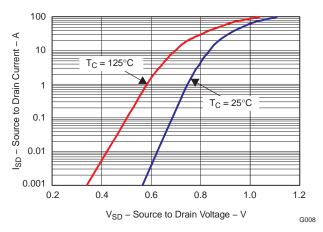


Figure 9. Typical Diode Forward Voltage

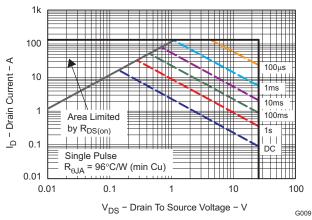


Figure 10. Maximum Safe Operating Area

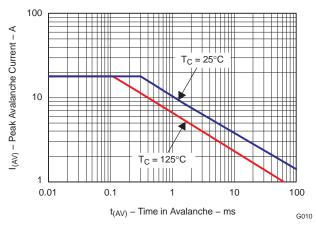


Figure 11. Single Pulse Unclamped Inductive Switching

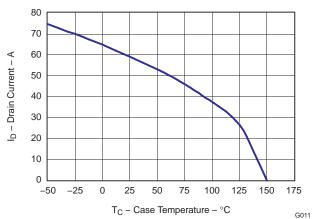
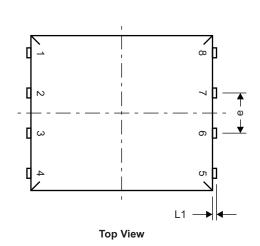


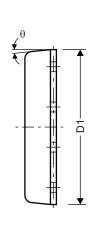
Figure 12. Maximum Drain Current vs. Temperature



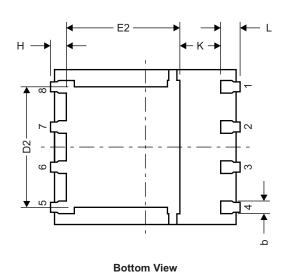
# **MECHANICAL DATA**

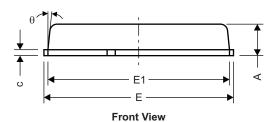
# **Q5A Package Dimensions**





Side View





M0135-01

DIM	MILLIMETERS						
	MIN	NOM	MAX				
Α	0.90	1.00	1.10				
b	0.33	0.41	0.51				
С	0.20	0.25	0.30				
D1	4.80	4.90	5.00				
D2	3.61	3.81	3.96				
Е	5.90	6.00	6.10				
E1	5.70	5.75	5.80				
E2	3.38	3.58	3.78				
е		1.27 BSC					
Н	0.41	0.51	0.61				
K	1.10						
L	0.51 0.61		0.71				
L1	0.06	0.13	0.20				
θ	0°		12°				

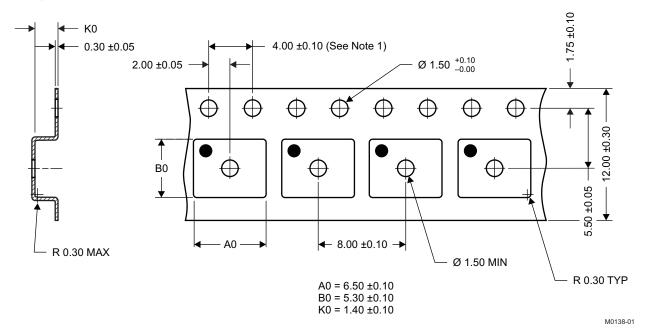


Recomme	nded PCB Pattern
F6 -	— F1 ——————————————————————————————————
F6	F7 F7
₩	710 — T M0139-01

DIM	MILLIN	METERS	INCHES		
DIIVI	MIN	MAX	MIN	MAX	
F1	6.205	6.305	0.244	0.248	
F2	4.46	4.56	0.176	0.18	
F3	4.46	4.56	0.176	0.18	
F4	0.65	0.7	0.026	0.028	
F5	0.62	0.67	0.024	0.026	
F6	0.63	0.68	0.025	0.027	
F7	0.7	0.8	0.028	0.031	
F8	0.65	0.7	0.026	0.028	
F9	0.62	0.67	0.024	0.026	
F10	4.9	5	0.193	0.197	
F11	4.46	4.56	0.176	0.18	

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

# **Q5A Tape and Reel Information**



## Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible

# SLPS205A - AUGUST 2009-REVISED MAY 2010



# **REVISION HISTORY**

CI	Page	
•	Deleted the Package Marking Information section	7

PACKAGE MATERIALS INFORMATION

www.ti.com 21-Mar-2013

# TAPE AND REEL INFORMATION





A0	
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

# QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



## \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16410Q5A	SON	DQJ	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

www.ti.com 21-Mar-2013



#### \*All dimensions are nominal

ĺ	Device	Device Package Type		Package Drawing Pins		Length (mm)	Width (mm)	Height (mm)	
	CSD16410Q5A	SON	DQJ	8	2500	340.0	340.0	38.0	

#### IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

#### Products Applications

Audio www.ti.com/audio Automotive and Transportation www.ti.com/automotive Communications and Telecom **Amplifiers** amplifier.ti.com www.ti.com/communications **Data Converters** dataconverter.ti.com Computers and Peripherals www.ti.com/computers **DLP® Products** www.dlp.com Consumer Electronics www.ti.com/consumer-apps

DSP **Energy and Lighting** dsp.ti.com www.ti.com/energy Clocks and Timers www.ti.com/clocks Industrial www.ti.com/industrial Interface interface.ti.com Medical www.ti.com/medical logic.ti.com Logic Security www.ti.com/security

Power Mgmt power.ti.com Space, Avionics and Defense www.ti.com/space-avionics-defense

Microcontrollers microcontroller.ti.com Video and Imaging www.ti.com/video

RFID www.ti-rfid.com

OMAP Applications Processors <a href="www.ti.com/omap">www.ti.com/omap</a> TI E2E Community <a href="e2e.ti.com">e2e.ti.com</a>

Wireless Connectivity <u>www.ti.com/wirelessconnectivity</u>